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Power Grid Analysis Challenges for Large Microprocessor Designs

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Contents

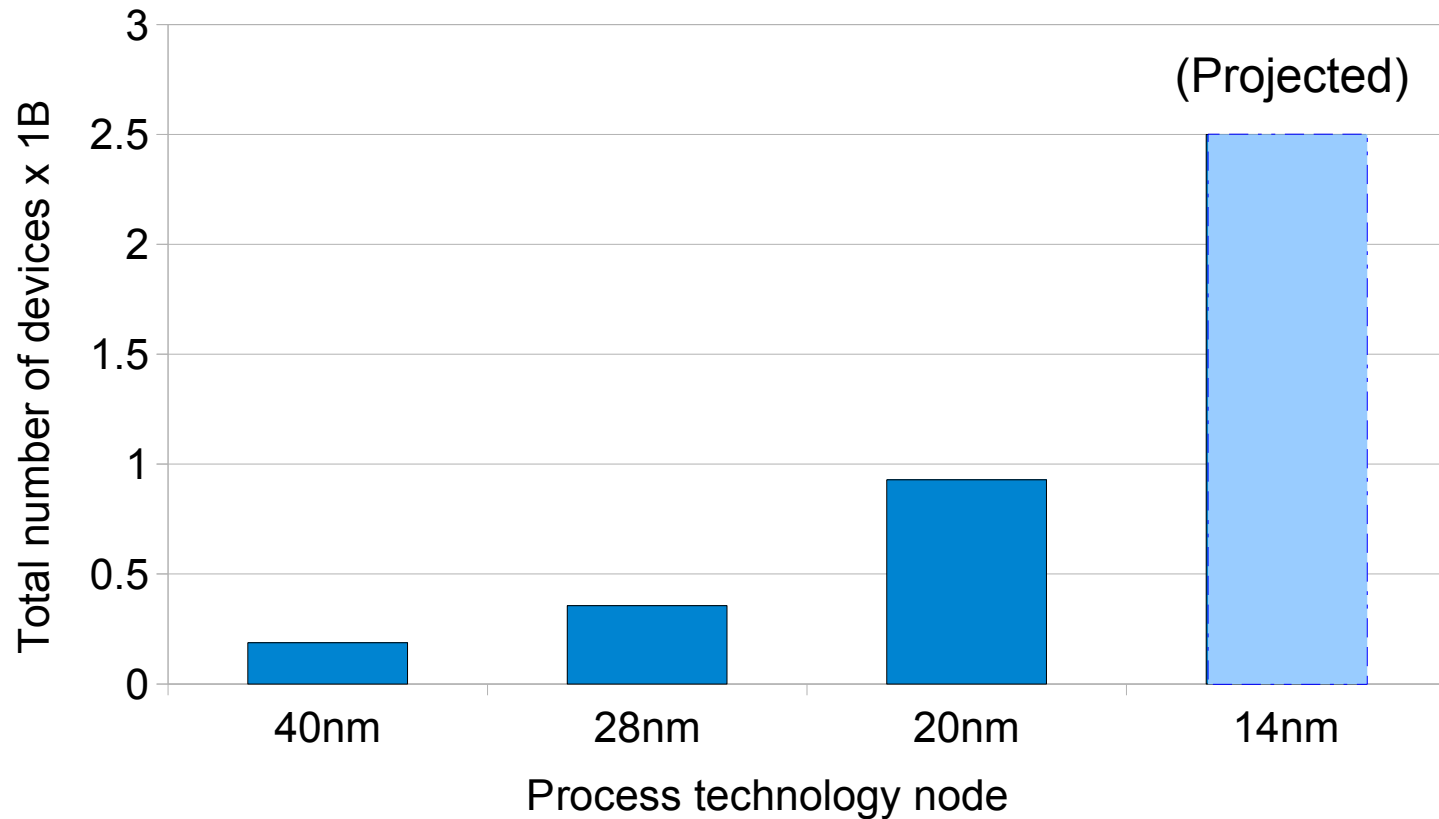
- Introduction
- Oracle Sparc design: data size and trend
- Power grid extraction challenges
- Early power grid analysis
- Bulk grid analysis challenges
- Design style: flat vs. hierarchical
- Simulation techniques
- Design debugging aid
- Future challenges
- Conclusions

Introduction

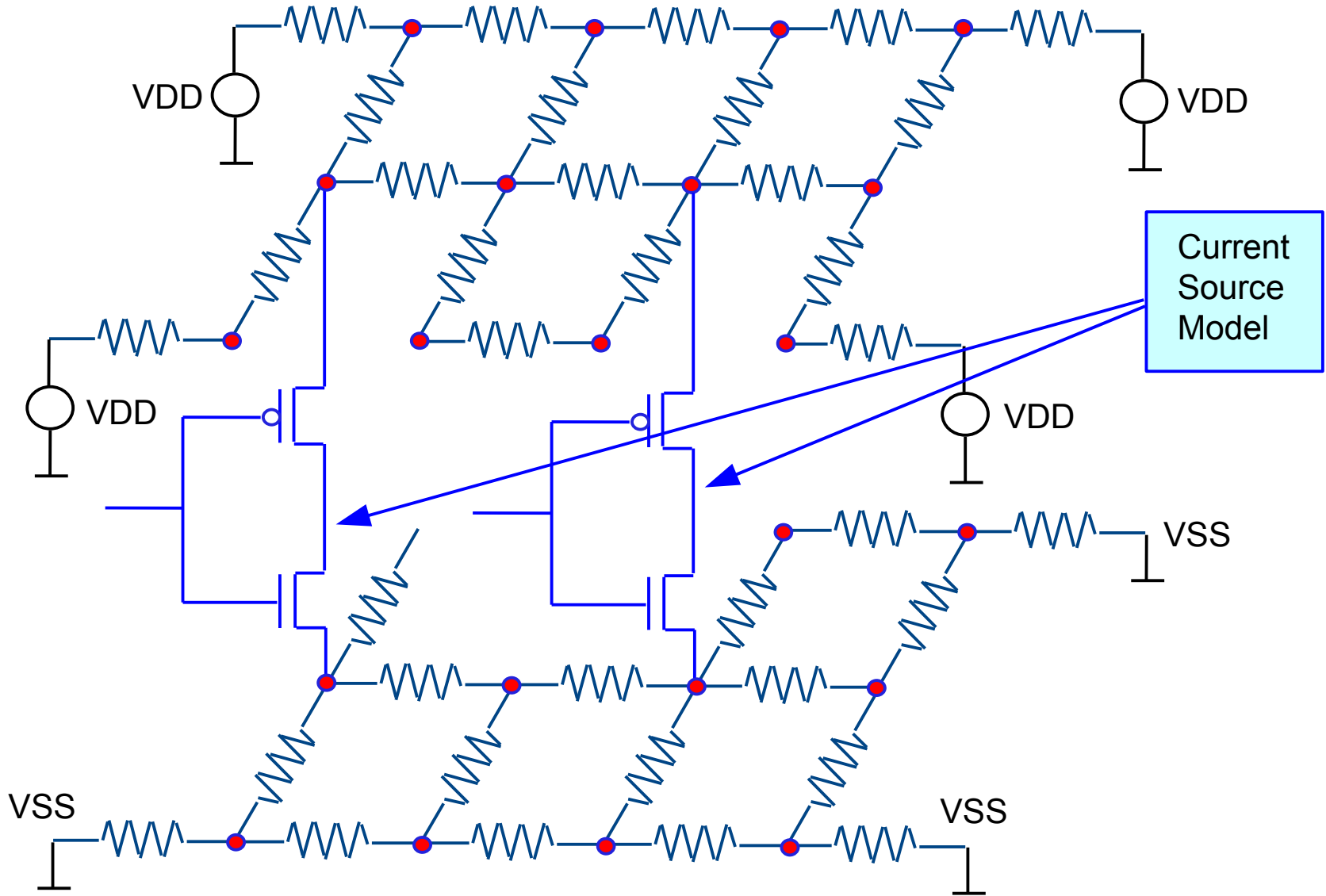
- Chip size and complexity has grown exponentially over the years
- Power distribution network (or power grid) is an extremely important component of processor design
- Power grid design and analysis is a very challenging task because of:
 - increasing complexity and operating frequency
 - shrinking feature size
 - sensitivity to supply voltage variations
 - low power demand
- Special purpose efficient high capacity tools set is required

Oracle Sparc Design: Data Size and Trend

Largest Block Size



Typical Power Grid Design



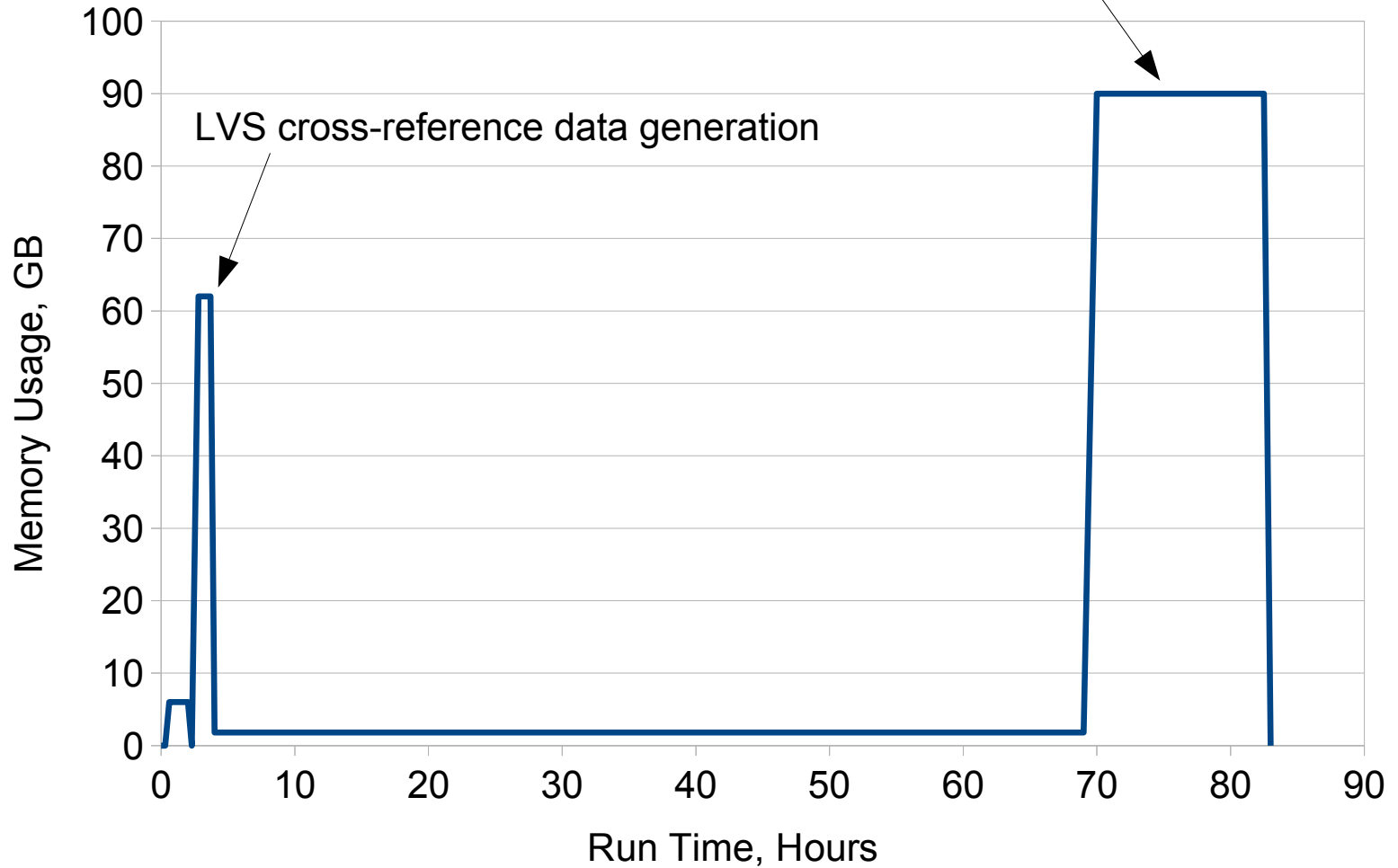
Power Grid Extraction Challenges

- Extraction is a critical part of design analysis sign-off methodology
- Meantime, it can be an extremely complex task due to the processor design size
- Severe run time and capacity issues has been identified when running EDA vendor extraction tools for large design with >1B resistors
- 14nm design will grow 2-3X in size
- High capacity demand needs to be addressed by extraction methodology and tools

Power Grid Extraction Challenges

Extraction Memory Usage Profile

Netlist generation (10.5 Hrs)

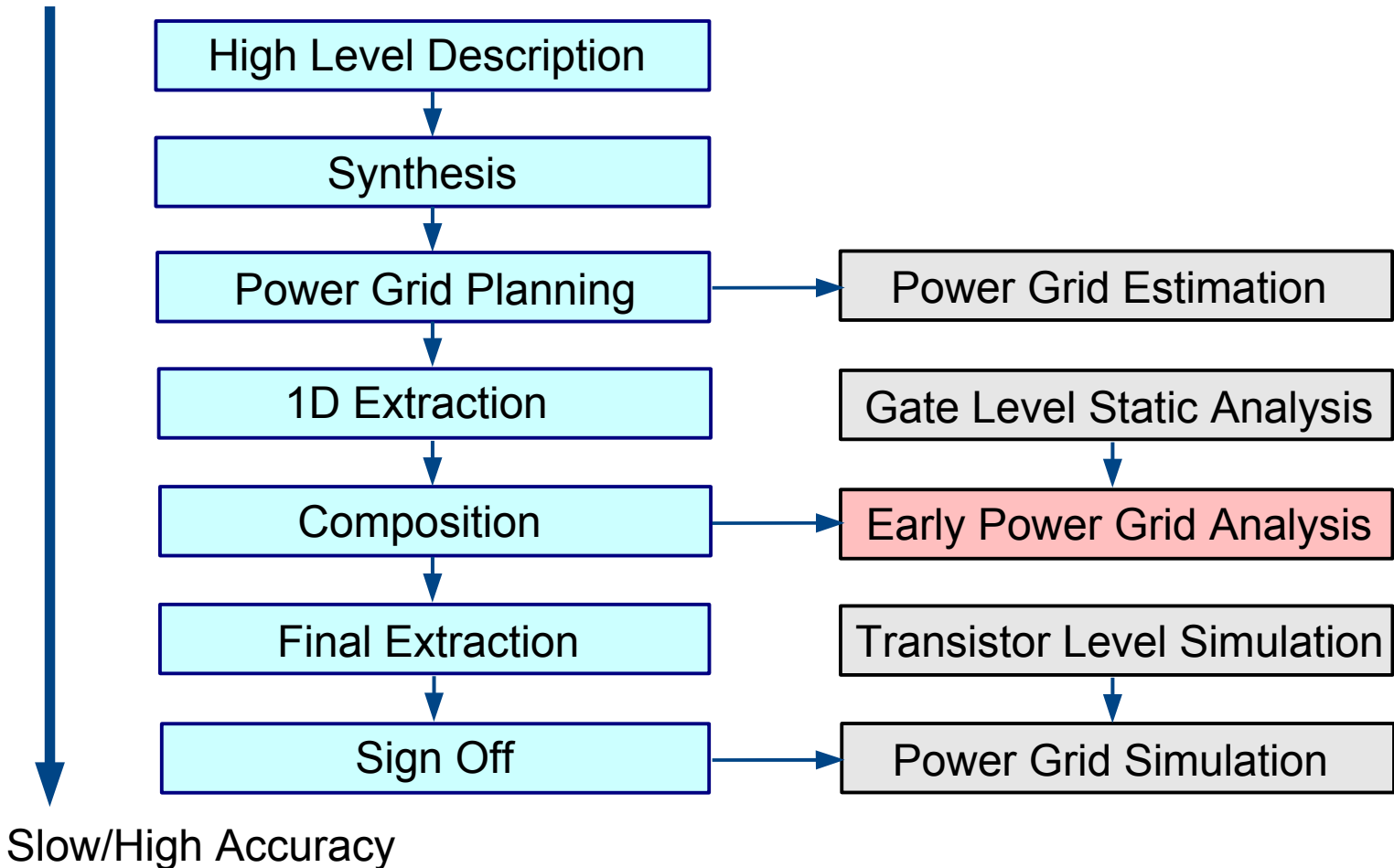


Why Early Power Grid Analysis?

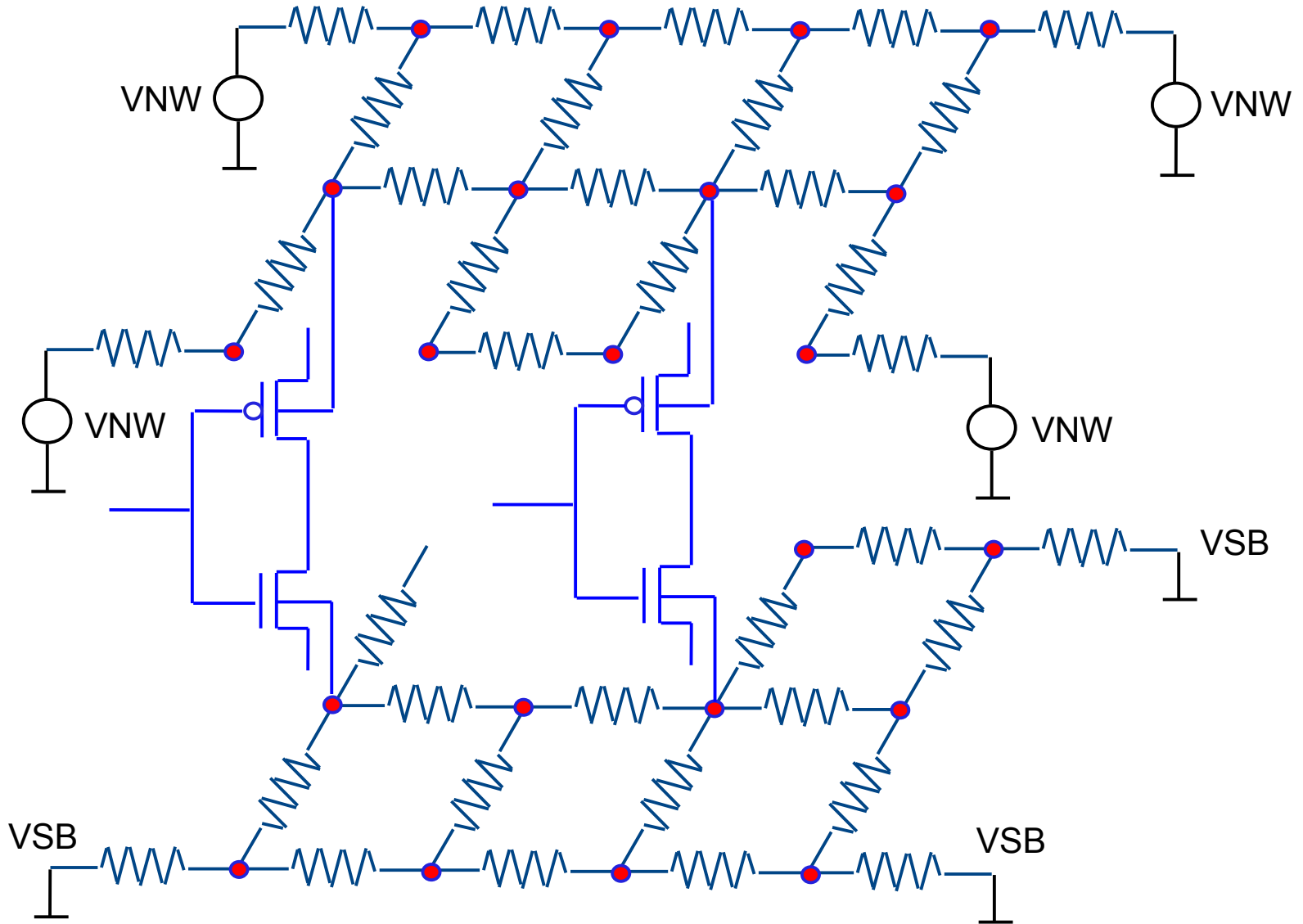
- Too many design iterations at signoff
- Full extraction runs into the performance and capacity issues
- Transistor level simulation for tap currents analysis is accurate but slow
- Methodology to refine power grid at various design stages [R.Panda, et.al., DAC-98]
- IR drop estimation at composition stage:
 - fast 1D extraction
 - gate level static analysis for tap currents
 - R-only power grid analysis

Early Power Grid Analysis

Fast/Low Accuracy

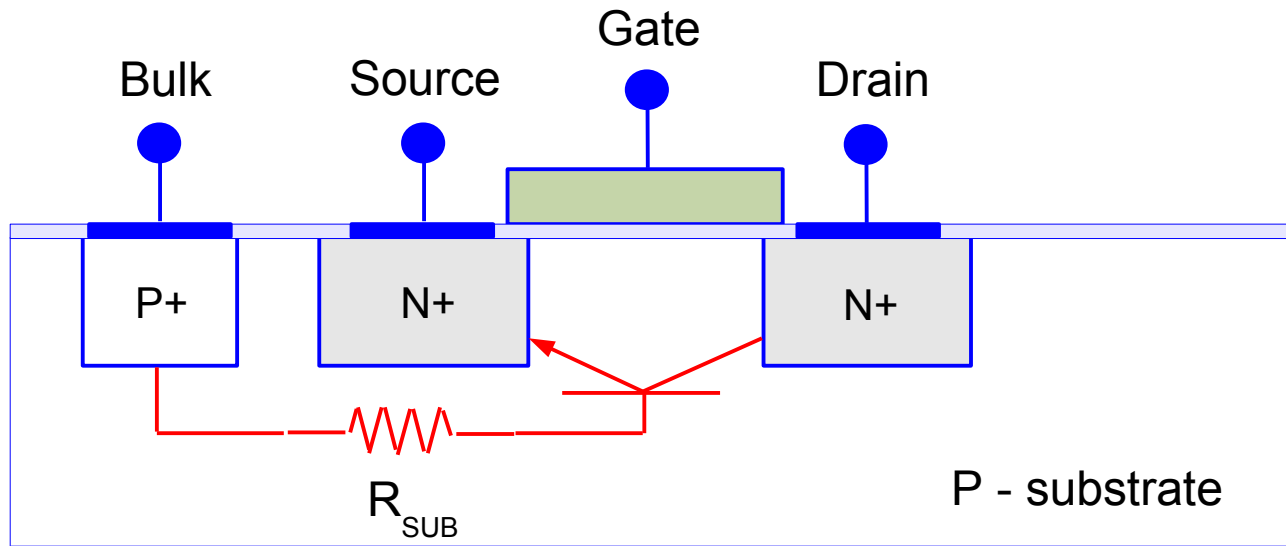


Bulk Grid Analysis



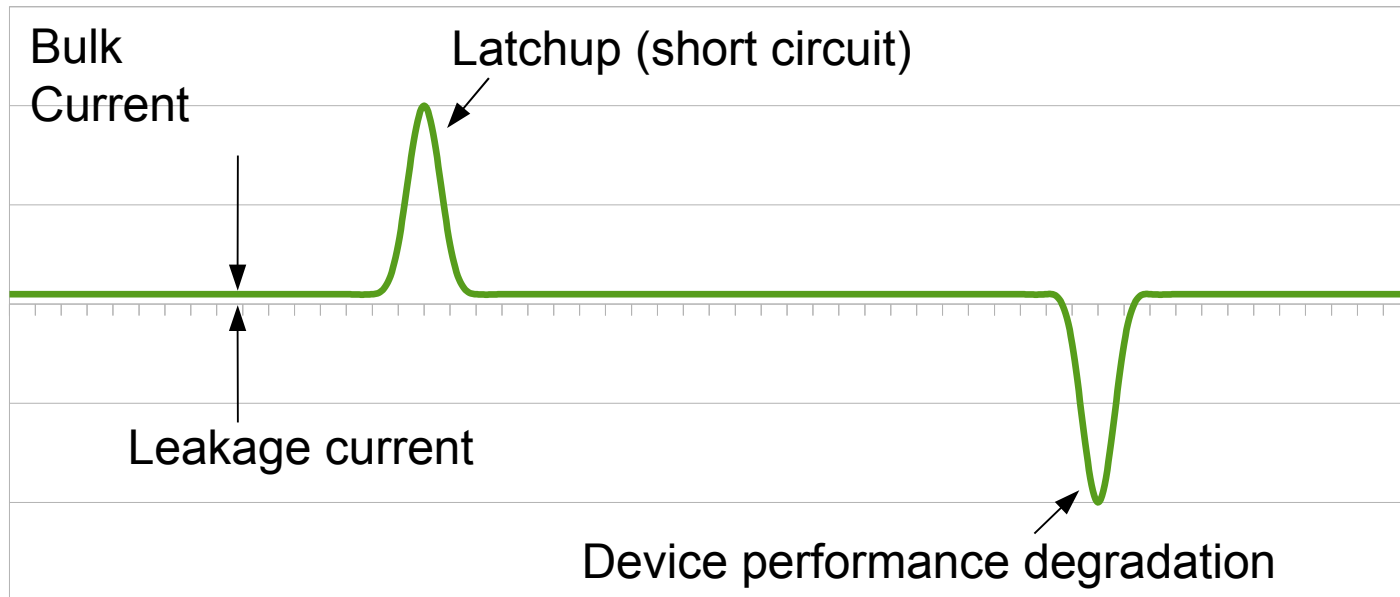
Bulk Grid Analysis Challenges

- Tap points for transistor currents are not localized: substrate resistance extraction is required



Bulk Grid Analysis Challenges

- Bidirectional switching large currents charging transistor capacitors must be analyzed along with small unidirectional leakage current
- Results interpretation is different from the regular power grid

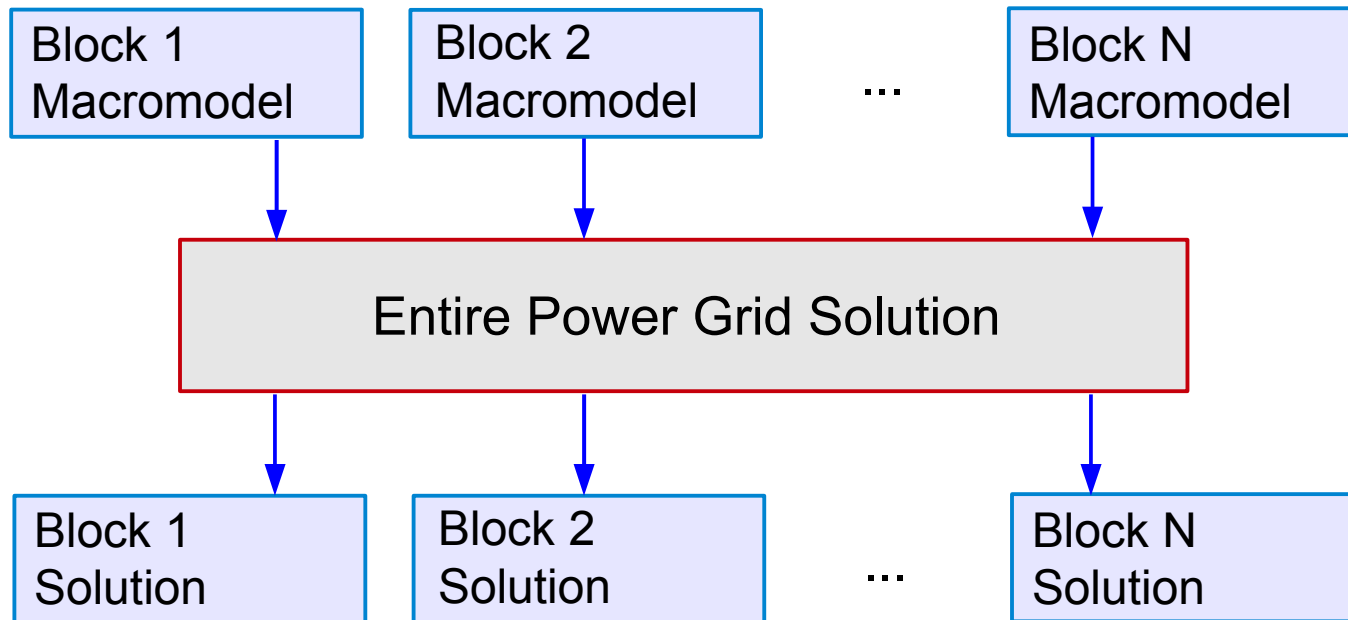


Design Style: Flat vs Hierarchical

- Hierarchical design is a natural solution for capacity problem
- However there are techniques made it attractive to compose a flat design down to library cells level:
 - advances in place and route technology
 - opportunities for accurate timing analysis
 - manual optimization
- Highest metal density areas placed within library cells helps to reduce the data size
- However the overall size is still too large
- Artificial hierarchy: introduces too many currents across the block boundaries

Simulation Techniques: Hierarchical

- Global and multiple local power grids
- Hierarchical power grid analysis [M.Zhao, et.al., DAC-2000]
- Block size and number of ports are rapidly growing



Simulation Techniques: Solutions

- Multigrid approach [F.Najm, et.al, ICCAD-2001]: fast, but not accurate, difficult to use for irregular structures
- Model Order Reduction [L.He, et.al., DAC-2006]: inefficient for the large number of ports
- Currents locality effect [E.Chiprout, et.al., ICCAD-2004; A.Korobkov, et.al., PIERS-2009]: better run time/accuracy tradeoff, but scalability is limited
- Iterative methods like Random walks [S.Nassif, et.al, DAC-2003], Successive over-relaxation [M.Wong, et.al., ICCAD-2005]: memory efficient and easy to parallelize but slow

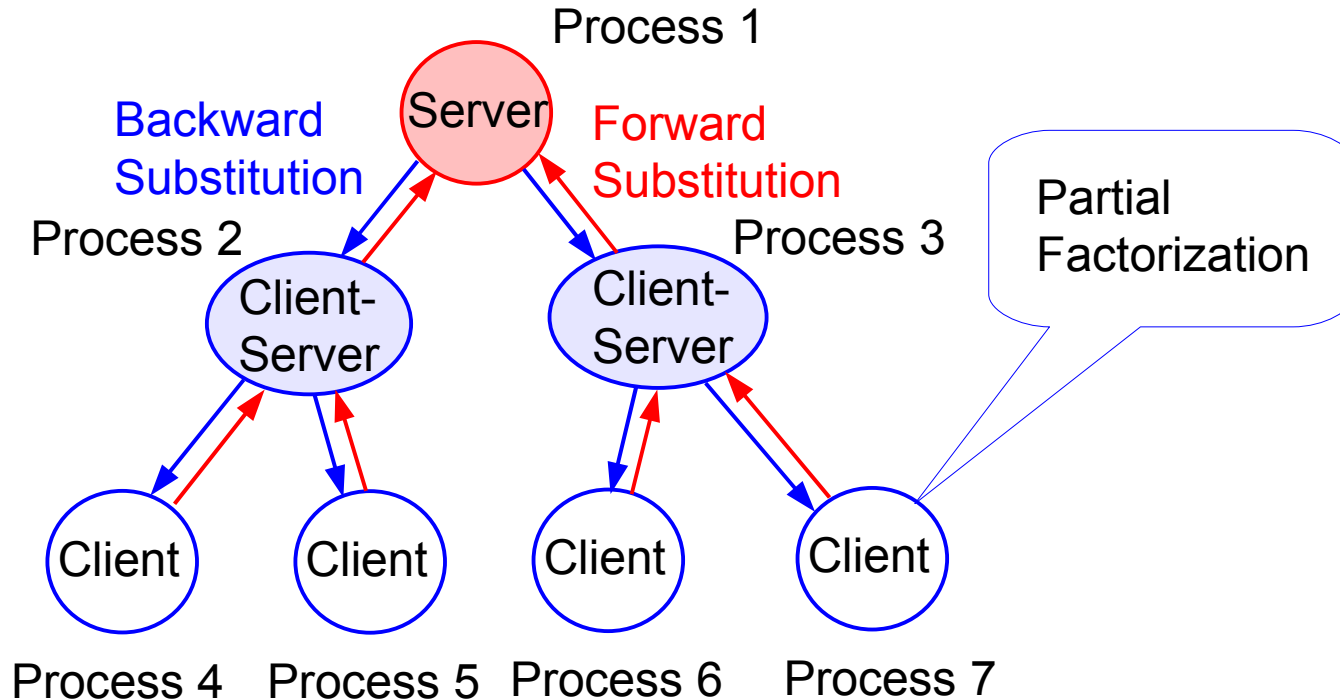
Simulation Techniques: Solutions

Direct Methods	Iterative Methods
Fast but memory inefficient and difficult to parallelize	Slow but memory efficient and easy to parallelize
Dynamic vector based analysis for smaller design	Static or pseudo-dynamic analysis for larger design
Memory usage can be addressed by efficient parallel distributed analysis with multiple processes	Performance can be addressed by the improved initial guess and parallel runs with multiple threads

- Transient analysis is problematic, however direct solver in combination with constant time step provide some improvement
- Combined direct and iterative methods does not provide much performance gain while use more memory and reduce opportunities for parallel execution

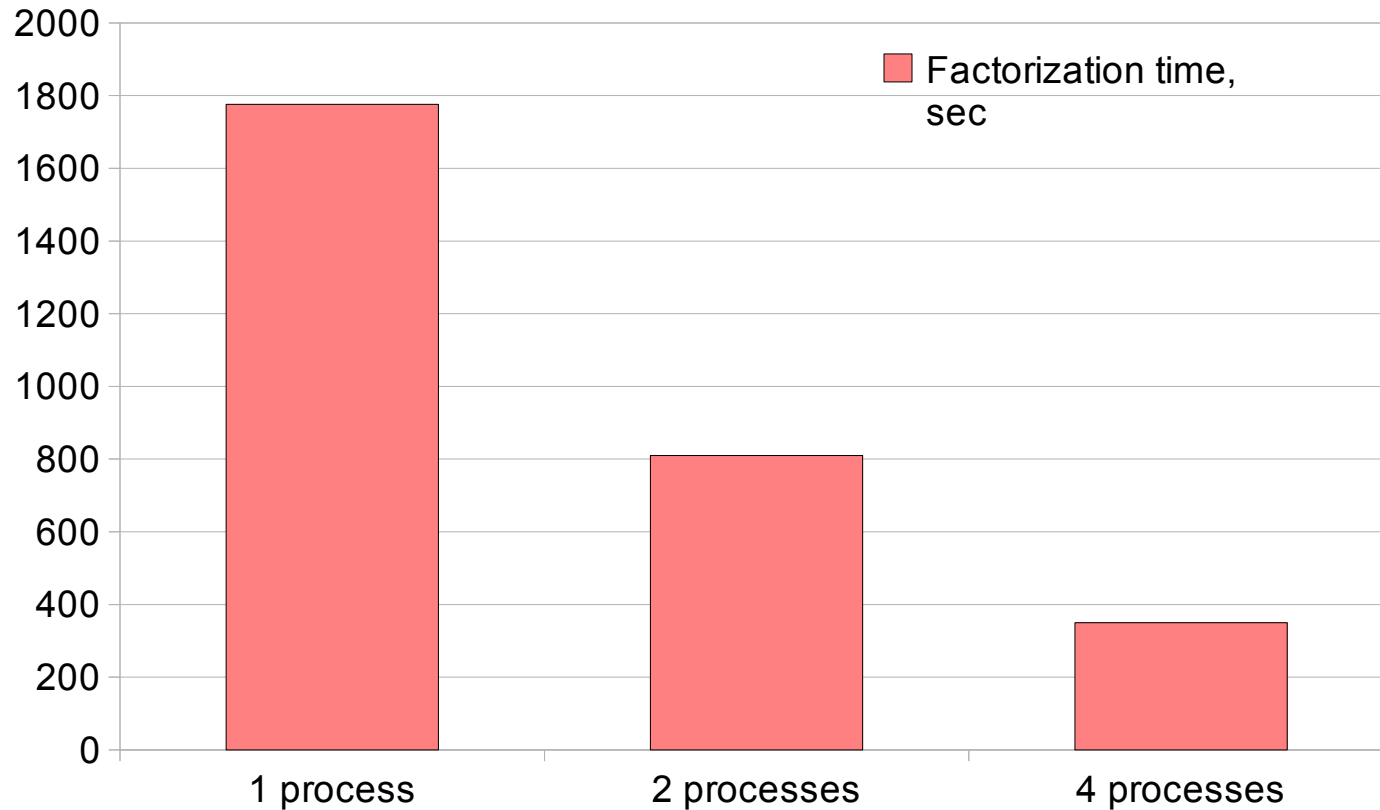
Simulation Techniques: Direct Solver

- Direct solver is fast, but how to reduce memory?
- Solution: distributed parallel linear solver
- Extensively used outside EDA (structural mechanics, fluid dynamics, etc.)



Distributed Linear Solver: Run Time

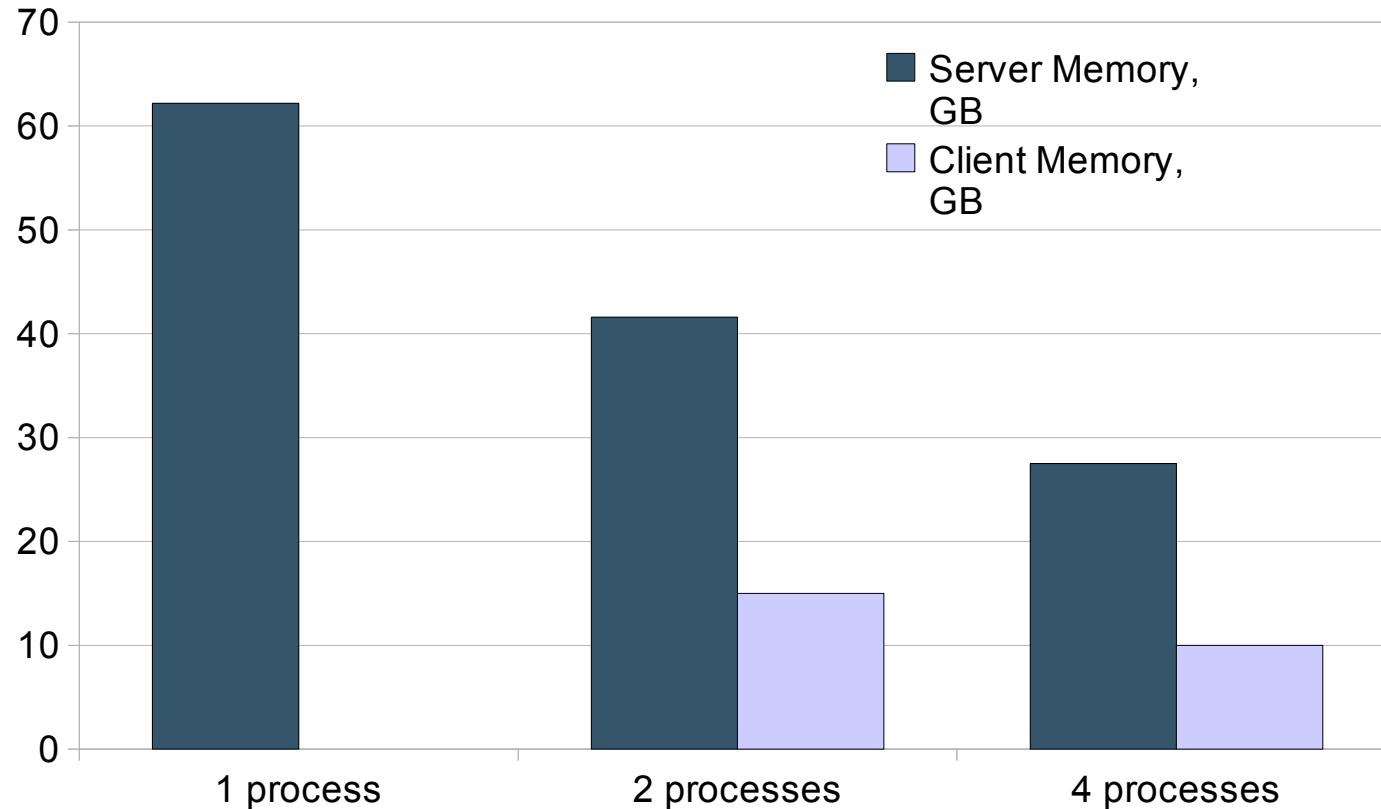
Block level power grid with 86M nodes, 356M devices



Expect similar scaling for larger blocks

Distributed Linear Solver: Memory

Block level power grid with 86M nodes, 356M devices



Expect similar scaling for larger blocks

Design Debugging Aid

- Layout editor capacity challenge
- Graphic interface overlay EM violations to layout
- Tracer between IR violation and source
- Automated fixer tools

The screenshot displays the SeeSharp software interface. The main window shows a layout editor with a grid overlay and various colored regions (yellow, red, grey) indicating EM violations. The interface includes a menu bar (File, View, Accentuate), a toolbar, and a status bar at the bottom showing "Status: Done." The right-hand side features a "Report / Query" window with a table of results and a "Layer and Element Selection" panel.

Report / Query

Queries	Name	(V) or (A)	Layer
Max 10 Node IR Drops	N_vdd...	0.02344	METAL_1
Max 25 Node IR Drops	N_vdd...	0.02343	METAL_1
Max 10 Resistor Currents	N_vdd...	0.02338	METAL_1
Max 25 Resistor Currents	N_vdd...	0.02337	METAL_1
Get All (Nodes)	N_vdd...	0.02325	METAL_1
Get All (Resistors)	N_vdd...	0.02323	METAL_1
Get All (Voltage Sources)	N_vdd...	0.02322	METAL_1
	N_vdd...	0.0232	METAL_1
	N_vdd...	0.02317	METAL_1

IR Drop and Resistor Current

Severity Bins

Node Leg...	Ranges (V...)	Resistor L...	Ranges (A...)
0	0.00403	0	0.09365
	0.00807		1.93386
	0.0121		3.77406
	0.01614		5.61427
	0.02017		7.45448
	0.02421		9.29468
	0.03228		11.13489
			14.8153

Layer and Element Selection

Display	Layer	Color	Bin (n...)	Bin(res)
<input checked="" type="checkbox"/>	METAL_1		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
<input type="checkbox"/>	YA1		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
<input type="checkbox"/>	METAL_2		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
<input type="checkbox"/>	YA2		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>

Vsrc Node Resistor

irDrop current

Select All Layers Select All Bins

Load

Future Challenges (14nm and Beyond)

- Growing design size and the number of devices will drive the power grid size
- More EM and IR issues due to:
 - higher frequency
 - reduced supply voltage
 - dynamically switching gated grids
 - narrower, thinner and longer wires
- Inductance will play more important role in extraction and analysis, along with package model
- More complex parasitics for 3D devices (FinFET), multiple new sources of variability
- FinFETs will dramatically increase power density: reliability and thermal analysis are required

Conclusions

- Power grid size for processor design is rapidly growing but EDA vendors are late to respond
- Parasitics extraction complexity is a challenge, tools and methodologies must comply
- Bulk grid analysis is an important part of the power grid analysis supported by the same tools set
- Hierarchical power grid design can help with both extraction and analysis but does not solve all issues
- There are multiple simulation strategies, but no perfect solution available
- Parallel and distributed execution is a must
- Many new challenges come up with 14nm process, need to be addressed as soon as possible

Q & A

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